

**Partial English Translation of**  
**LAID OPEN unexamined**  
**JAPANESE PATENT APPLICATION**  
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[0075] Further, although Ar ions are beforehand implanted into a region where metal silicide is to be formed in each of the aforementioned embodiments, any ions are usable as long as the ions to be implanted are not conductive when implanted in SiO<sub>2</sub>. For example, ions of helium (He), xenon (Xe), krypton (Kr), neon (Ne), radon (Rn), nitrogen (N), oxygen (O), carbon (C), silicon (Si) are usable instead of Ar ions. Wherein, arsenic (As), boron (B), phosphorus (P) and antimony (Sb), which each generally serve as a dopant into Si, are not usable.